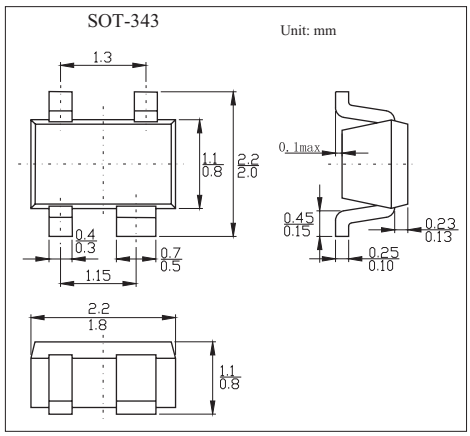
Silicon Switching Diode Array

BAS28W



■ Features

- For high-speed switching applications
- Electrical insulated diodes

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	75	V
Peak reverse voltage	V_{RM}	85	V
Forward current	I_F	200	mA
Surge forward current, t = 1 μs	I_{FS}	4.5	A
Total power dissipation, Ts = 103℃	P_{tot}	250	mW
Junction temperature	T_j	150	℃
Storage temperature range	T_{stg}	-55 to + 150	℃
Junction - ambient [1)]	$R_{th\ JA}$	⩽ 460	K/W
Junction - soldering point	$R_{th\ JS}$	⩽ 190	K/W

Note

1.Package mounted on epoxy pcb 40mm × 40mm × 1.5mm / 0.5cm^2 Cu

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■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Breakdown voltage	$I_{(BR)}$	V_R = 40 V	85			V
Forward voltage	I_F	I_F = 1 mA			715	mV
		I_F = 10 mA			855	
		I_F = 50 mA			1000	
		I_F = 150 mA			1250	
Reverse current	I_R	V_R = 75 V			1	μA
		V_R = 25 V, T_A = 150℃			30	
		V_R = 75 V, T_A = 150℃			50	
Diode capacitance	C_D	f = 1 MHz; V_R = 0			2	pF
Reverse recovery time	t_{rr}	I_F = 10 mA, I_R = 10 mA, R_L = 100 Ω measured at I_R = 1mA			6	ns

■ Marking

Marking	JTs